



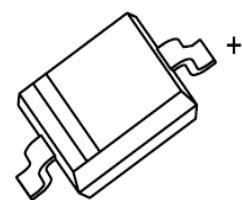
迈拓电子
MAITUO ELECTRONIC

RB501W-40 Schottky Barrier Diode

FEATURES

- Low current rectifier schottky diode
- Low voltage, low inductance
- For power supply

MAKING: 4



SOD-123

Maximum Ratings and Electrical Characteristics, Single Diode @Ta=25°C

Parameter	Symbol	Limit		Unit
Peak reverse voltage	V _{RM}	45		V
DC reverse voltage	V _R	40		V
Mean rectifying current	I _O	0.1		A
Non-repetitive Peak Forward Surge Current@t=8.3ms	I _{FSM}	1		A
Power dissipation	P _D	200		mW
Thermal Resistance Junction to Ambient	R _{θJA}	500		°C/W
Junction temperature	T _j	125		°C
Storage temperature	T _{stg}	-55~+150		°C

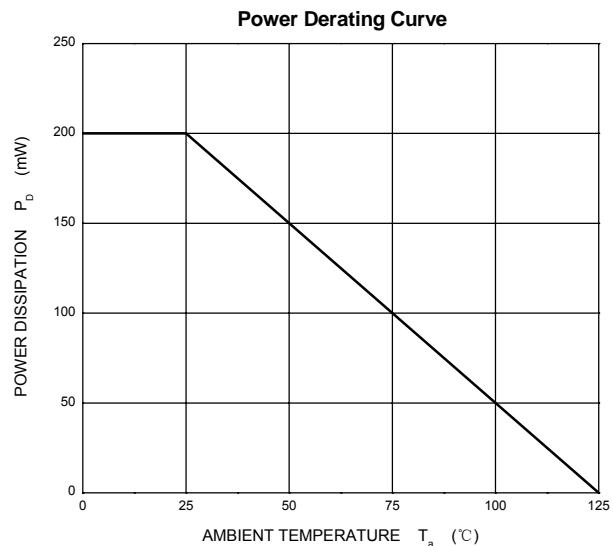
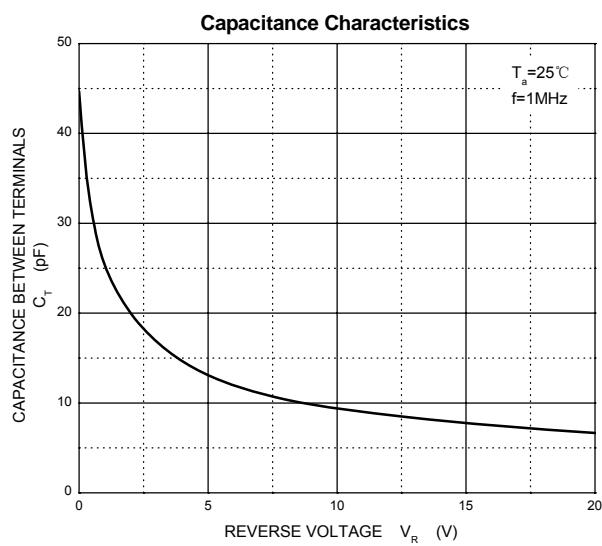
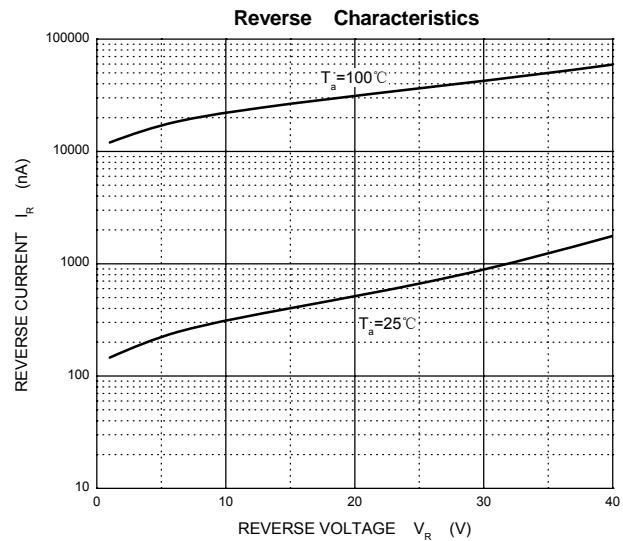
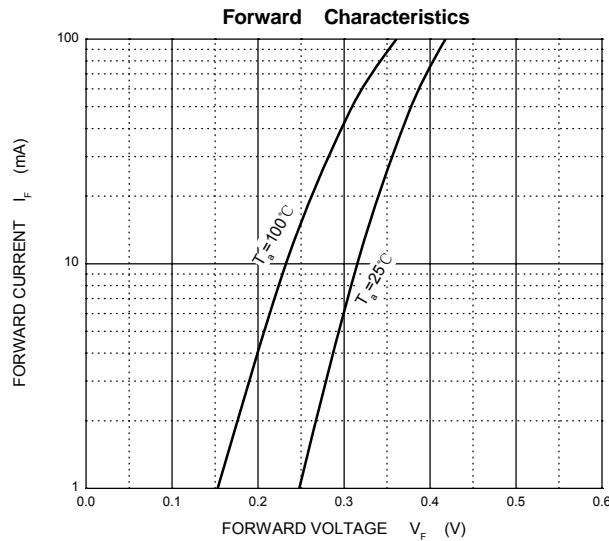
Electrical Ratings @Ta=25°C

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Forward voltage	V _F			0.55 0.34	V	I _F =100mA I _F =10mA
Reverse current	I _R			30	μA	V _R =10V
Capacitance between terminals	C _T		6		pF	V _R =10V, f=1MHZ



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Typical Characteristics



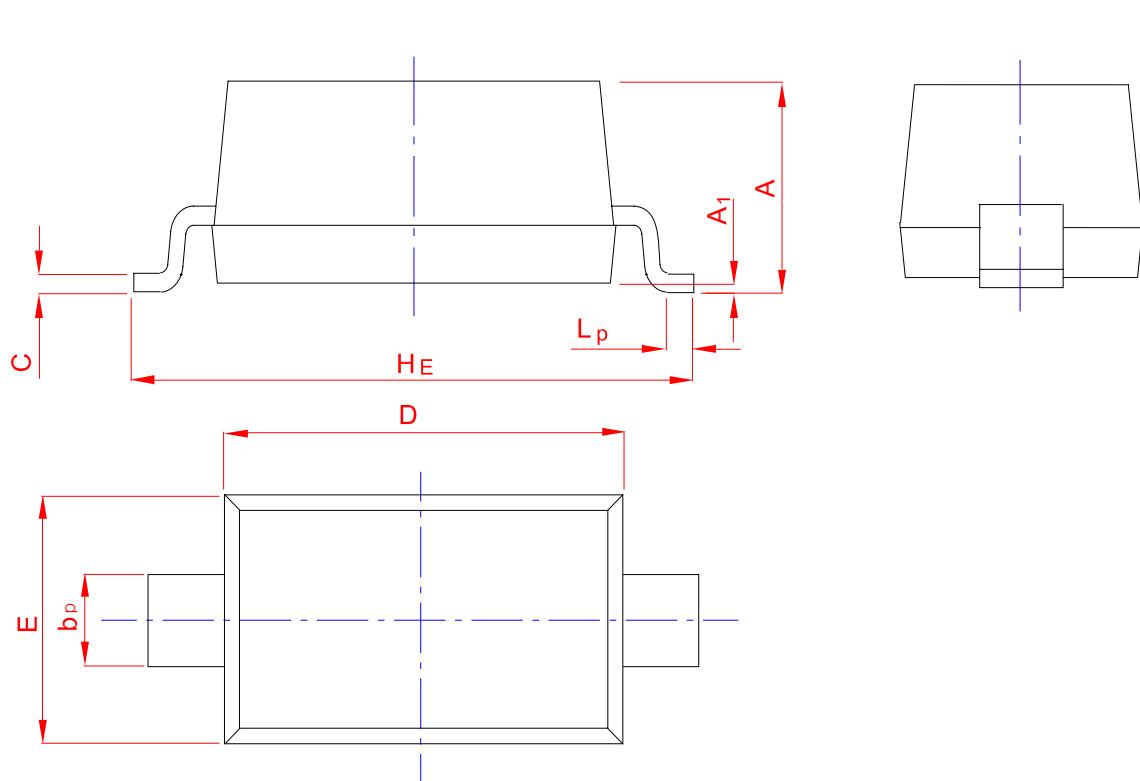


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PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

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UNIT	A	b _p	C	D	E	H _E	A ₁	L _p
mm	1.20 0.90	0.60 0.50	0.135 0.100	2.75 2.55	1.65 1.55	3.85 3.55	0.10 0.01	0.50 0.20